

### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

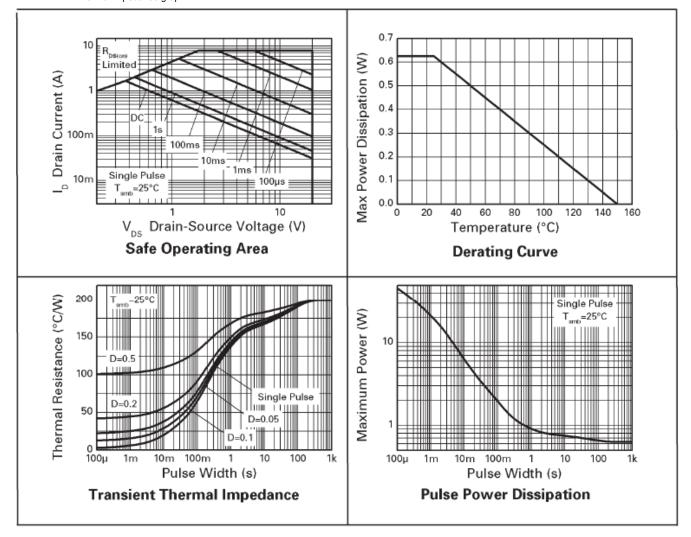
Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Continuous Drain Current, V <sub>GS</sub> = 10V	(Note 6) (Note 6) (Note 5)	$T_A = +25$ °C $T_A = +70$ °C $T_A = +25$ °C	I <sub>D</sub>	2.2 1.7 1.9	А
Pulsed Drain Current (Note 7)			I <sub>DM</sub>	8	Α
Maximum Body Diode Continuous Current (Note 6)			Is	1.29	Α
Maximum Body Diode Continuous Current (Note 7)			I <sub>SM</sub>	8	Α

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 5)	6	625	mW	
Linear Derating Factor	(Note 5)	P <sub>D</sub>	5	mW/°C	
Total Power Dissipation	(Note 6)	6	806	mW	
Linear Derating Factor	(Note 6)	$P_{D}$	6.4	mW/°C	
Thermal Desigtance, Junction to Ambient	(Note 5)	0	200	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	155		
Operating and Storage Temperature Range	•	$T_{J_1}T_{STG}$	-55 to +150	°C	

Notes:

- 5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- 6. For a device surface mounted on FR-4 PCB measured at t≤5 secs.
- 7. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05, pulse width 10µs pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.





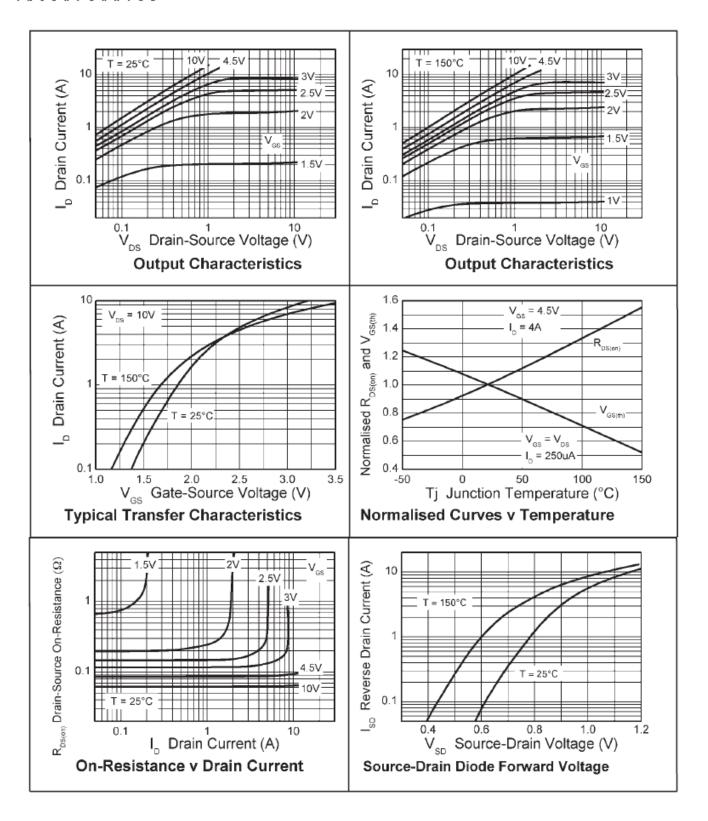
#### Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_		V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Body Leakage	Igss	_	_	100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(th)}$	0.7	_	_	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance (Note 8)	R <sub>DS(ON)</sub>	_	_	0.12	Ω	$V_{GS} = 4.5V, I_D = 4A$	
Static Drain-Source On-Resistance (Note 6)		_	_	0.225	Ω	$V_{GS} = 2.5V, I_D = 1.5A$	
Forward Transconductance	g <sub>FS</sub>	_	6.1	_	S	$V_{DS} = 10V, I_{D} = 4A$	
Diode Forward Voltage (Note 8 & 10)	$V_{SD}$	_	0.85	0.95	V	$V_{GS} = 0V$ , $I_S = 3.2A$ , $T_J = +25$ °C	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	303	_	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	59				
Reverse Transfer Capacitance	C <sub>rss</sub>	_	30	_			
Total Gate Charge (Note 9)	Qg	_	3.0	_		101/1/	
Gate-Source Charge (Note 9)	$Q_{gs}$	_	0.8	_	nC	$V_{DS} = 10V, V_{GS} = 10V,$ $I_{D} = 4A$	
Gate-Drain Charge (Note 9)	$Q_{gd}$	_	1.0	_			
Turn-On Delay Time (Note 9)	t <sub>D(on)</sub>	_	2.49	_			
Turn-On Rise Time (Note 9)	t <sub>r</sub>	_	5.21	_		$V_{DD} = 10V$ , $I_D = 4A$ , $R_G = 6\Omega$ , $V_{GS} = 5V$	
Turn-Off Delay Time (Note 9)	t <sub>D(off)</sub>	_	7.47	_	ns		
Turn-Off Fall Time (Note 9)	t <sub>f</sub>		4.62	_			
Reverse Recovery Time	t <sub>rr</sub>	_	23	_	ns	T .0500 L 4A 45/44 4004/5	
Reverse Recovery Charge	Qrr	_	5.65	_	nC	$T_J = +25$ °C, $I_F = 4A$ , di/dt= 100A/ $\mu$ s	

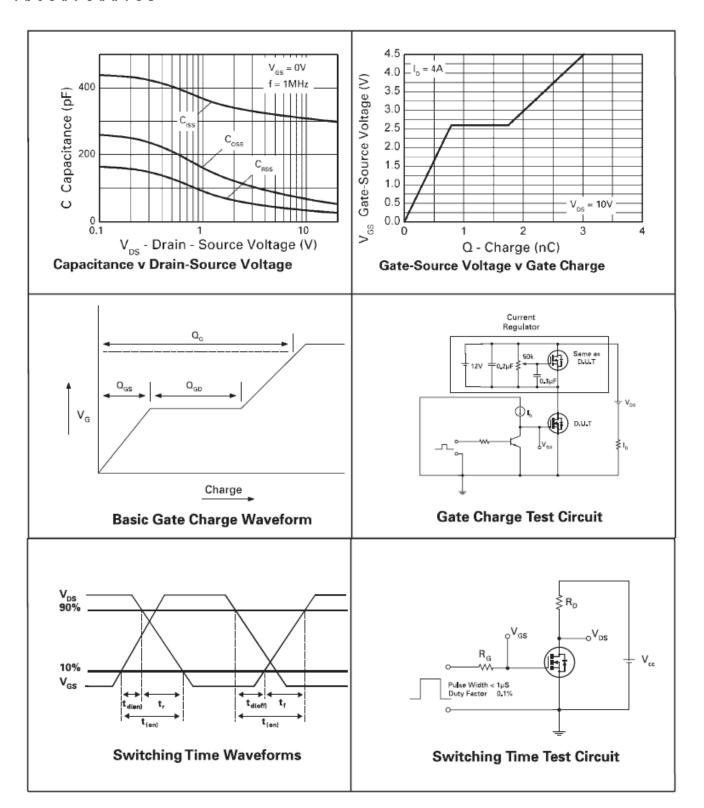
Notes:

- 8. Measured under pulsed conditions. Width=300µs. Duty cycle ≤ 2%.
  9. Switching characteristics are independent of operating junction temperature.
  10. Guaranteed by design. Not subject to production testing.





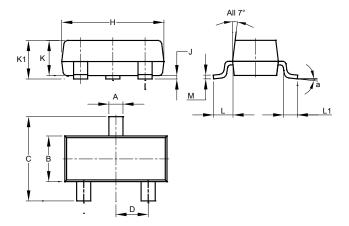






## **Package Outline Dimensions**

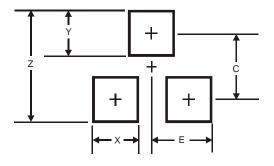
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
M	0.085	0.150	0.110			
а	8°					
All Dimensions in mm						

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
F	1.35



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